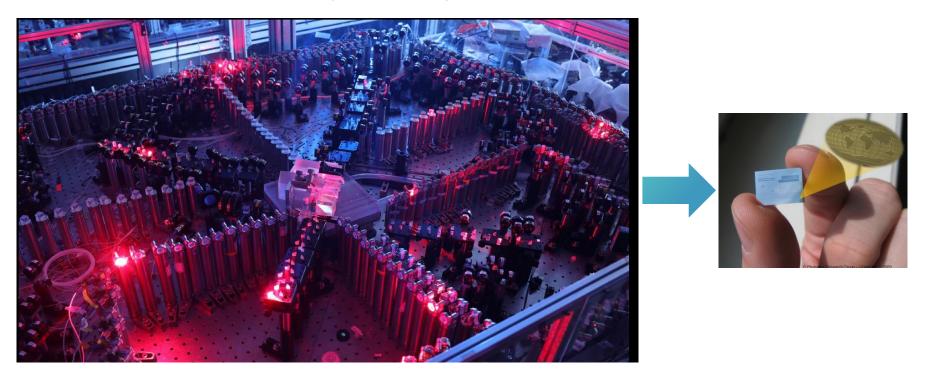




SCALABILITY CONCERN

Moving from 10s qBit toward 1000s, 10K, ...



H. Zhong, et al, "Quantum computational advantage using photons", Science, 2020.



200 MM & 300 MM CLEANROOMS (24/7 OPERATION)













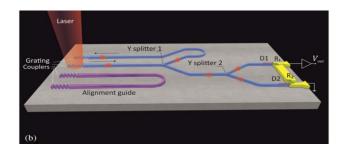


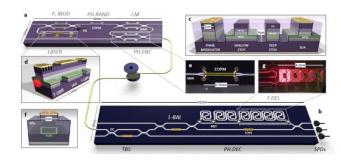
QKD: USING PHOTONICS





- Ultrafast quantum random number generation (QRNG)
- Entangled photonic integrated sources
- Inter-connection (3D integration) between multiple chips





A, Gaggero, Amp-multiplexed readout of single photon detectors superconducting nanowires, 2019. P. Sibson, et al, "Chip-based Quantum Key Distribution", 2015.





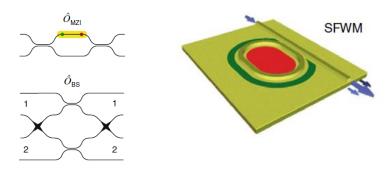
SIN IS THE ENABLER TECHNOLOGY FOR QC

Basic building blocks

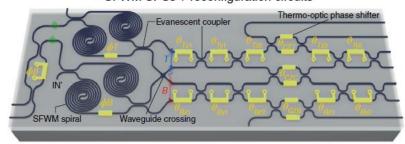
- PIC based quantum processor
- High Q ring resonators
- MZ interferometer-switch
- Phase shifters (Thermal, LiNbO3, etc.)
- In-out coupling interfaces

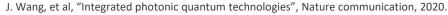
SiN features

- Scalable 200/300 mm wafer production
- Extremely low loss (down to few dB/m)
- Low phase noise
- Transparent at visible wavelength (ion-trapping)
- High power handling



SFWM SPSs + reconfiguration circuits



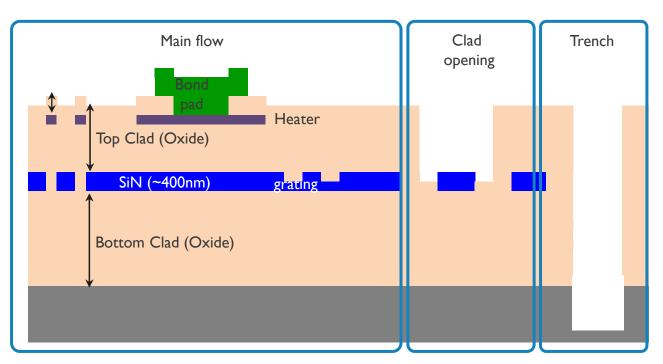


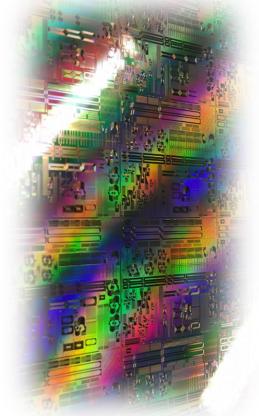




FLEXIBLE CROSS SECTION FOR DIFFERENT USE-CASES

HIGH VOLUME MANUFACTURING





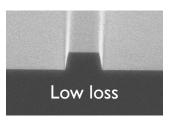




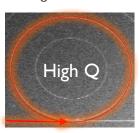
SIN PHOTONICS PLATFORM @ IMEC

A large library of experimentally verified components is available

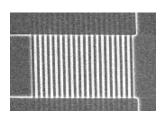
Waveguides



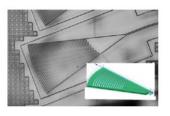
Ring Resonators



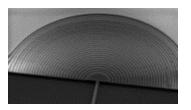
Fiber-to-WG



Low reflection

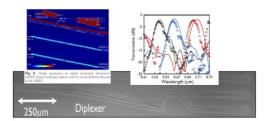


Focusing

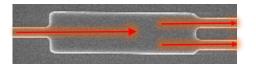


Basic spectrometers

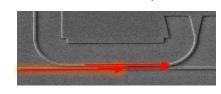




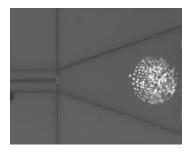
Multi-mode interferometer



Evanescent coupler



Pseudo-random



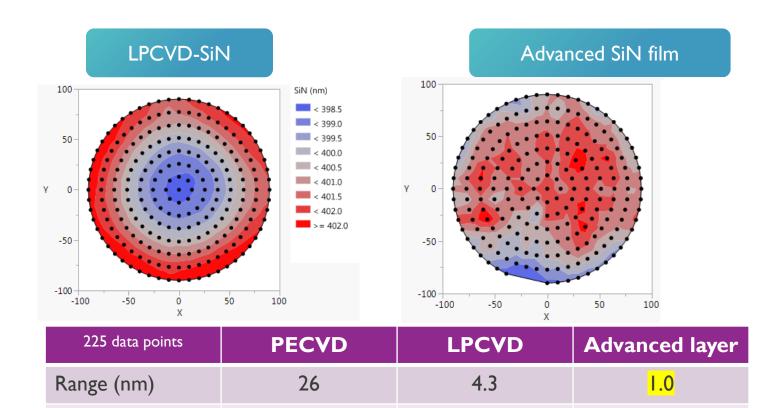








UNIFORMITY ON 200MM WAFER



0.58

2.85

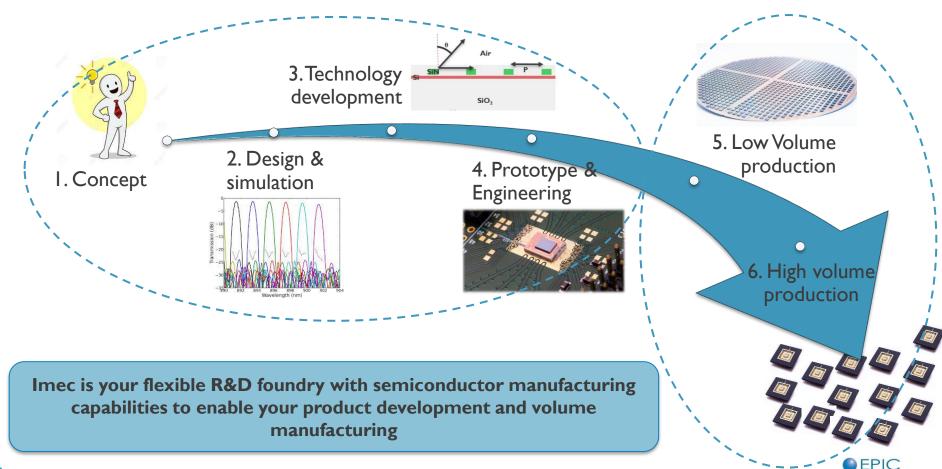


0.06



% th/std dev

R&D INDUSTRIAL HUB DEDICATED TO OPTICAL BEAM FORMING



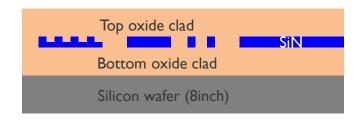
mec

embracing a better life

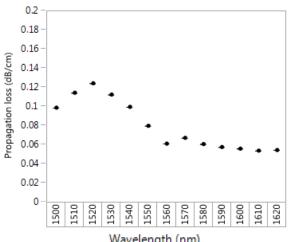
Amin.Abbasi@imec.be

SIN PHOTONICS PLATFORM HIGH VOLUME MANUFACTURING

- Extremely low propagation loss
 - Annealing of silicon nitride
 - Low waveguide sidewall roughness
- SiN layer
 - LPCVD stochiometric film
 - Hydrogen content control
 - Refractive index uniformity
 - Thickness uniformity
 - Shallow & full SiN etch
- Oxide layer
 - Refractive index uniformity



Propagation loss of a single mode waveguide



Wavelength (nm)

Higher absorption loss at 1520nm linked to N-H bond reduced from 3dB/cm (standard processing) down to 0.13dB/cm **PUBLIC**



ACTIVE DEVICE HYBRID INTEGRATION

- Hybrid integration enables to use the best features of each technology
 - SiN or Si for passive, switching, routing, coupling, etc.
 - IIIV for active devices, e.g. laser, modulator, photodiode
- Prototype could be developed via R&D contract
 - Technology-transfer to an industrial fab for production

